

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary) Sheet of 11

	Complete If Known
Application Number	10/801,499
Filing Date	March 15, 2004
First Named Inventor	Calafut, Daniel
Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	018865-015200US

	U.S. PATENT DOCUMENTS+										
Examiner Initials*	Cite No.	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Unes, Where Relevant Passages or Relevant Figures Appear						
A. U	AA	US-3,404,295	10-01-1968	Warner et al.							
1	AB	US-3,412,297	11-19-1968	Amlinger							
	AC	US-3,497,777	02-24-1970	Teszner et al.							
	AD	US-3,564,356	02-16-1971	Wilson							
	AE	US-4,003,072	01-11-1977	Matsushita et al.							
	AF	US-4,300,150	11-10-1981	Colak							
	AG	US-4,326,332	04-27-1982	Kenney et al.							
	AH	US-4,337,474	06-29-1982	Yukimoto							
	Al	US-4,579,621	04-01-1986	Hine							
	AJ	US-4,636,281	01-13-1987	Buiguez et al.							
	AK	US-4,638,344	01-20-1987	Cardwell, Jr.							
	AL	US-4,639,761	01-27-1987	Singer et al.							
	AM	US-4,698,653	10-06-1987	Cardwell, Jr.							
	AN	US-4,716,126	12-29-1987	Cogan							
	AO	US-4,746,630	05-24-1988	Hui et al.							
	AP	US-4,754,310	06-28-1988	Сое							
	AQ	US-4,774,556	09-27-1988	Fujii et al.							
	AR	US-4,801,986	01-31-1989	Chang et al.							
	AS	US-4,821,095	04-11-1989	Temple							
	AT	US-4,823,176	04-18-1989	Baliga et al.							
	AU	US-4,853,345	08-01-1989	Himelick							
	AV	US-4,868,624	09-19-1989	Grung et al.							
	AW	US-4,893,160	01-09-1990	. Blanchard							
	AX	US-4,914,058	04-03-1990	Blanchard							
	AY	US-4,941,026	07-10-1990	Temple							
	AZ	US-4,967,245	10-30-1990	Cogan et al.							
	BA	US-4,974,059	11-27-1990	Kinzer							
	BB	US-4,990,463	02-05-1991	Mori							
	BC	US-4,992,390	02-12-1991	Hsueh-Rong Chang							
	BD	US-5,027,180	06-25-1991	Nishizawa et al.							
	BE	US-5,071,782	12-10-1991	Mori							
	BF	US-5,072,266	12-10-1991	Buluccea							
	BG	US-5,079,608	01-07-1992	Wodarczyk et al.							
	вн	US-5,105,243	04-14-1992	Nakagawa et al.							
	BI	US 5,111,253	05-05-1992	Korman et al.							
	BJ	US-5,142,640	08-25-1992	Iwanatsu							
	BK	US-5,164,325	11-17-1992	Cogan et al.							
	BL	US-5,164,802	11-17-1992	Jones et al.							
	ВМ	US-5,216,275	06-01-1993	Chen							
	BN	US-5,219,777	06-15-1993	Kang	·						

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Examiner				Date	1,710,7	l
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached.

Substitu	ite for form 1449A/P	то		Complete If Known			
				Application Number	10/801,499		
INF	ORMATION	N DIS	SCLOSURE	Filing Date	March 15, 2004		
STA	TEMENT I	BY A	PPLICANT	First Named Inventor	Calafut, Daniel		
. 1				Art Unit	Not Yet Assigned		
L	(use as many sl	heets a	s necessary)	Examiner Name	Not Yet Assigned		
Sheet	2	of	11	Attorney Docket Number	018865-015200US		

	U.S. PATENT DOCUMENTS+									
Examiner Initials*	Cite No.1	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Unes, Where Relevant Passages or Relevant Figures Appear					
M.A	ВО	US-5,219,793	06-15-1993	Cooper et al.						
	BP	US-5,233,215	08-03-1993	Baliga						
	BQ	US-5,262,336	11-16-1993	Pike, Jr. et al.						
	BR	US-5,268,311	12-07-1993	Euen et al.						
	BS	US-5,275,965	01-04-1994	Manning						
	BT	US-5,294,824	03-15-1994	Okada						
	BU	US-5,298,761	03-29-1994	Cogan et al.						
	BV	US-5,300,447	04-05-1994	Anderson						
	ВW	US-5,326,711	07-05-1994	Malhi						
	BX	US-5,350,937	09-27-1994	Yamazaki et al.						
	BY	US-5,365,102	11-15-1994	Mehrotra et al.						
	BZ	US-5,366,914	11-22-1994	Takahashi et al.						
	CA	US-5,389,815	02-14-1995	Takahashi						
	СВ	US-5,405,794	04-11-1995	Kim						
	CC	US-5,418,376	05-23-1995	Muraoka et al.						
	CD	US-5,424,231	06-13-1995	Yang						
	CE	US-5,429,977	07-04-1995	Lu et al.						
	CF	US-5,430,311	07-04-1995	Murakami et al.						
	CG	US-5,430,324	07-04-1995	Bencuya						
	СН	US-5,436,189	07-25-1995	Beasom						
	CI	US-5,438,215	08-01-1995	Tihanyi						
	CJ	US-5,442,214	08-15-1995	Yang						
	CK	US-5,454,435	07-18-1995	Baliga						
	CL	US-5,473,176	12-05-1995	Kakumoto						
	СМ	US-5,473,180	12-05-1995	Ludikhuize						
	CN	US-5,474,943	12-12-1995	Hshieh et al.						
	co	US-5,519,245	05-21-1996	Tokura et al.						
	CP	US-5,541,425	07-30-1996	Nishihara						
	ca	US-5,554,862	09-10-1996	Omura et al.						
	CR	US-5,567,634	10-22-1996	Hebert et al.						
_	CS	US-5,567,635	10-22-1996	Acovic et al.						
	CT	US-5,572,048	11-05-1996	Sugawara						
	CU	US-5,576,245	11-19-1996	Cogan et al.						
	CV	US-5,578,851	11-26-1996	Hshieh et al.						
	CW	US-5,581,100	12-03-1996	Ajit						
	CX	US-5,583,065	12-10-1996	Miwa						
	CY	US-5,592,005	01-07-1997	Floyd et al.						
	CZ	US-5,595,927	01-21-1997	Chen et al.						
	DA	US-5,597,765	01-28-1997	Yilmaz et al.						
	DB	US-5,605,852	- 02-25-1997	Bencuya						

Examiner Signature	ANH	D.	WA	Date Considered	10/17	12005

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Substitute for form 1449A/PT	0	Complete If Known			
		Application Number	10/801,499		
INFORMATION	DISCLOSURE	Filing Date	March 15, 2004		
STATEMENT B	Y APPLICANT	First Named Inventor	Calafut, Daniel		
		Art Unit	Not Yet Assigned		
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Sheet 3	of 11	Attorney Docket Number	018865-015200US		

U.S. PATENT DOCUMENTS+												
	Document Number Distriction Date Name of Patenting of P											
Examiner Initials*	Cite No.1	Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentae or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear							
A. M	DC	US-5,623,152	04-22-1997	Majumdar et al.								
	DD	US-5,629,543	05-13-1997	Hshleh et al.								
	DE	US-5,637,898	06-10-1997	Baliga								
	DF	US-5,639,676	06-17-1997	Hshieh et al.								
	DG	US-5,640,034	07-17-1997	Satwinder Malhi								
	DH	US-5,648,670	07-15-1997	Blanchard								
	DI	US-5,656,843	08-12-1997	Goodyear et al.								
	DJ	US-5,665,619	09-09-1997	Kwan et al.								
	DK	US-5,670,803	09-23-1997	Beilstein, Jr. et al.								
	DL	US-5,689,128	11-18-1997	Hshieh et al.								
	DM	US-5,693,569	12-02-1997	Ueno								
	DN	US-5,705,409	01-06-1998	Witek								
	DO	US-5,710,072	01-20-1998	Krautschneider et al.	•							
	DP	US-5,714,781	02-03-1998	Yamamoto et al.								
	DQ	US-5,719,409	02-17-1998	Singh et al.								
	DR	US-5,770,878	06-23-1998	Beasom								
	DS	US-5,776,813	07-07-1998	Huang et al.								
	DT	US-5,780,343	07-14-1998	Bashir								
	DU	US-5,801,417	09-01-1998	Tsang et al.								
	DV	US-5,877,528	03-02-1999	So								
	DW	US-5,879,971	03-09-1999	Witek								
	DX	US-5,879,994	03-09-1999	· Kwan et al.								
	DY	US-5,895,951	04-20-1999	So et al.								
	DZ	US-5,895,952	04-20-1999	Darwish et al.								
	EA	US-5,897,343	04-27-1999	Mathew et al.								
	EB	US-5,897,360	04-27-1999	Kawaguchi								
	EC	US-5,900,663	05-04-1999	Johnson et al.								
	ED	US-5,906,680	05-25-1999	Meyerson								
	EE	US-5,917,216	06-29-1999	Floyd et al.								
	EF	US-5,929,481	07-27-1999	Hsieh et al.								
	EG	US-5,943,581	08-24-1999	Lu et al.								
	EH	US-5,949,104	09-07-1999	D'Anna et al.								
	ΕI	US-5,949,124	09-07-1999	Hadizad et al.								
	EJ	US-5,959,324	09-28-1999	Kohyama								
	EK	US-5,960,271	09-28-1999	Wollesen et al.								
	EL	US-5,972,741	10-26-1999	Kubo et al.								
	EM	US-5,973,360	10-26-1999	Tihanyi								
	EN	US-5,976,936	11-02-1999	Miyajima et al.								
	EO	US-5,981,344	11-09-1999	Hshieh et al.								
	EP	US-5,981,996	11-09-1999	Fujishima								

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Substitu	Substitute for form 1449A/PTO			Complete if Known			
				Application Number	10/801,499		
INFO	ORMATION	V DIS	SCLOSURE	Filing Date	March 15, 2004		
STA	TEMENT E	BY A	PPLICANT	First Named Inventor	Calafut, Daniel		
				Art Unit	Not Yet Assigned		
1	(use as many sh	heets as	s necessary)	Examiner Name	Not Yet Assigned		
Sheet	4	of	11	Attorney Docket Number	018865-015200US		

	U.S. PATENT DOCUMENTS+										
		Document Number			Dance Columns (Jane Milana						
Examiner Initials*	Cite No.1	Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear						
A.M	EQ	US-5,998,833	12-07-1999	Baliga							
	ER	US-6,005,271	12-21-1999	Hshieh							
	ES	US-6,008,097	12-28-1999	. Yoon et al.							
	ET	US-6,011,298	01-04-2000	Blanchard							
	ΕU	US-6,015,727	01-18-2000	Wanlass							
	ΕV	US-6,020,250	02-01-2000	Kenny et al.							
	EW	US-6,034,415	05-07-2000	Johnson et al.							
	EX	US-6,037,202	03-14-2000	Witek							
	EY	US-6,037,628	03-14-2000	Huang							
	EZ	US-6,037,632	03-14-2000	Omura et al.							
	FA	US-6,040,600	03-21-2000	Uenishi et al.							
	FB	US-6,048,772	04-11-2000	D'Anna							
	FC	US-6,049,108	04-11-2000	Williams et al.							
	FD	US-6,057,558	05-02-2000	Yamamoto et al.							
	FE	US-6,063,678	05-16-2000	D'Anna							
	FF	US-6,064,088	05-16-2000	D'Anna							
	FG	US-6,066,878	05-23-2000	Neilson							
	FH	US-6,081,009 .	06-27-2000	Neilson							
	FI	US-6,084,264	07-04-2000	Darwish							
	FJ	US-6,084,268	07-04-2000	de Frésart et al.							
	FK	US-6,087,232	07-11-2000	Kim et al.	·						
	FL	US-6,096,608	08-01-2000	· Williams ·							
	FM	US-6,097,063	08-01-2000	Fujihira							
	FN	US-6,103,578	08-15-2000	Uenishi et al.							
	FO	US-6,104,054	08-15-2000	Corsi et al.							
	FP	US-6.110.799	08-29-2000	Huang							
	FQ	US-6,114,727	09-05-2000	Ogura et al.							
	FR	US-6,137,152	10-24-2000	Wu							
	FS	US-6,156,606	12-05-2000	Michaelis							
	FT	US-6,156,611	12-05-2000	Lan et al.							
	FU	US-6,163,052	12-19-2000	Liu et al.							
	FV	US-6,165,870	12-26-2000	Shim et al.							
	FW	US-6,168,983	01-02-2001	Rumennik et al.							
	FX	US-6,168,996	01-02-2001	Numazawa et al.							
	FY	US-6,171,935	01-09-2001	Nance et al.							
	FZ	US-6,174,773	01-16-2001	Fujishima							
	GA	US-6,174,785	01-16-2001	Parekh et al.							
	GB	US-6,184,545	02-06-2001	Werner et al.	·						
	GC	US-6,184,555	02-06-2001	Tihanyi et al.							
	GD	US-6,188,104	02-13-2001	Choi et al.							

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Examiner Signature	ANH	D.	MAi	Date Considered	10	17	2005

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Substitute for form 1449A/PTO		Complete If Known
	Application Number	10/801,499
INFORMATION DISCLOSURE	Filing Date	March 15, 2004
STATEMENT BY APPLICANT	First Named Inventor	Calafut, Daniel
	Art Unit	Not Yet Assigned
(use as many sheets as necessary)	Examiner Name	Not Yet Assigned
Sheet 5 of 11	Attorney Docket Number	018865-015200US

			U.S. PATENT DO	CUMENTS+	
Examiner Initials*	Cite No.	Document Number Number Kind Code ² (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
A. M	GE	US-6,188,105	02-13-2001	Kocon et al.	
1	GF	US-6,190,978	02-20-2001	D'Anna .	
	GG	US-6,191,447	02-20-2001	Baliga	
	GH	US-6,198,127	03-06-2001	Kocon	
	GI	US-6,201,279	03-13-2001	Pfirsch	
	GJ	US-6,204,097	03-20-2001	Shen et al.	
.	GK	US-6,207,994	03-27-2001	Rumennik et al.	
	GL	US-6,222,233	04-24-2001	D'Anna	
	GM	US-6,225,649	05-01-2001	Minato	
	GN	US-6,228,727	05-08-2001	Lim et al.	
	GO	US-6,239,464	05-29-2001	Tsuchitani et al.	
	GP	US-6,265,269	07-24-2001	Chen et al.	
	GQ	US-6,271,100	08-07-2001	Ballantine et al.	
	GR	US-6,271,552	08-07-2001	D'Anna	
	GS	US-6,271,562	08-07-2001	Deboy et al.	
	GT	US-6,274,905	08-14-2001	Mo	
	GU	US-6,277,706	08-21-2001	Ishikawa	
	GV	US-6,285,060	09-04-2001	Korec et al.	
	GW	US-6,291,298	09-18-2001	Williams et al.	
	GX	US-6,291,856	09-18-2001	Miyasaka et al.	
	GY	US-6,294,818	09-25-2001	Fujihira	
	GZ	US-6,297,534	10-02-2001	Kawaguchi et al.	
	НА	US-6,303,969	10-16-2001	Tan	
	НВ	US-6,307,246	10-23-2001	Nitta et al	
	HC	US-6,309,920	10-30-2001	Laska et al.	
	HD	US-6,313,482	11-06-2001	Baliga	
	HE	US-6,326,656	12-04-2001	Tihanyi	
	HF	US-6,337,499	01-08-2002	Werner	
	HG	US-6,346,464	02-12-2002	Takeda et al	
	· HH	US-6,346,469	02-12-2002	Greer	
	HI	US-6,351,018	02-26-2002	Sapp	
	HJ	US-6,353,252	03-05-2002	Yasuhara et al.	
	НК	US-6,359,308	03-19-2002	Hijzen et al.	
	HL	US-6,362,112	03-26-2002	Hamerski	
	НМ	US-6,362,505	03-26-2002	Tihanyi	
	HN	US-6,365,462	04-02-2002	Baliga	
	но	US-6,365,930	04-02-2002	Schillaci et al.	
	HP	US-6,368,920	04-09-2002	Beasom	
-	HQ	US-6,368,921	04-09-2002	Hijzen et al	
	HR	US-6,376,314	04-23-2002	Jerred	

Signature 77.0 D. P.	Examiner Signature	ANH	۵.	MAI	Date Considered	10	1,7	12005
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INFO	ORMATION	1 DIS	SCLOSURE	Filing Date	March 15, 2004
STA	TEMENT E	BY A	PPLICANT	First Named Inventor	Calafut, Daniel
				Art Unit	Not Yet Assigned
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Sheet	6	of	11	Attorney Docket Number	018865-015200US

			U.S. PATENT DO	CUMENTS+	
Examiner Initials*	Cite No.	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Unes, Where Relevant Passages or Relevant Figures Appear
A.M	HS	US-6,376,878	04-23-2002	Kocon	
1	HT	US-6,376,890	04-23-2002	Tihanyi	
	HU	US-6,384,456	05-07-2002	Tihanyl	
	HV	US-6,388,286	05-14-2002	. Baliga	
	HW	US-6,388,287	05-14-2002	Deboy et al.	
	HX	US-6,400,003	06-04-2002	Huang	
	HY	US-6,429,481 B1	08-06-2002	Mo et al.	
	HZ	US-6,433,385	08-13-2002	Kocon et al.	
	IA	US-6,436,779	08-20-2002	Hurkx et al.	
	IB	US-6,437,399	08-20-2002	Huang	
	IC	US-6,441,454	08-27-2002	Hijzen et al.	
	ID	US-6,452,230	09-17-2002	Boden, Jr.	
	ΙE	US-6,465,304	10-15-2002	Blanchard et al.	
	IF	US-6,465,843	10-15-2002	Hirler et al.	
	IG	US-6,465,869	10-15-2002	Ahlers et al.	
	IH	US-6,472,678	10-29-2002	Hshieh et al.	
	11	US-6.472,708	10-29-2002	Hshieh et al.	
_	IJ	US-6,475,884	11-05-2002	Hshieh et al.	
	IK	US-6,476,443	11-05-2002	Kinzer	
	IL	US-6,479,352	11-12-2002	Blanchard	
	IM	US-6,489,652 B1	12-03-2002	Jeon et al.	
	IN	US-6,501,146	12-31-2002	Harada	
	10	US-2001/0023961 A1	09-27-2001	Hsieh et al.	
	IP	US-2001/0028083 A1	10-11-2001	Onishi et al.	
	IQ	US-2001/0032998 A1	10-25-2001	Iwamoto et al.	
	IR	US-2001/0041400 A1	11-15-2001	Ren et al.	
-+-	IS	US-2001/0049167 A1	12-06-2001	Madson	
	ΙΤ	US-2001/0050394 A1	12-13-2001	Onishi et al.	
	ΙU	US-2002/0009832 A1	01-24-2002	Blanchard	
	IV	US-2002/0014658 A1	02-07-2002	Blanchard	
	IW	US-2002/0066924 A1	06-06-2002	Blanchard	
	ΙX	US-2002/0070418 A1	06-13-2002	Kinzer et al.	
	ΙΥ	US-2003/0060013 A1	03-27-2003	Marchant	
	IZ	US-2003/0100933	08-01-2002	Marchant	
	JA	US-2003/0100933 A1	08-01-2002	Marchant	
	JB	US-2003/0193067 A1	10-16-2003	Kim	
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Examiner Signature	ANH	D.	MAi	Date Considered	10/17/2005

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INFORMATION DISCLOSUR	E Filing Date	March 15, 2004			
STATEMENT BY APPLICAN	First Named Inventor	Calafut, Daniel			
	Art Unit	Not Yet Assigned			
(use as many sheets as necessary)	Examiner Name	Not Yet Assigned			
Sheet 7 , of 11	Attorney Docket Number	018865-015200US			

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Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached.

Substitu	ite for form 1449A/P1	го			Complete If Known
	•			Application Number	10/801,499
INF	ORMATION	1 DIS	SCLOSURE	Filing Date	March 15, 2004
STA	TEMENT E	BY A	PPLICANT	First Named Inventor	Calafut, Daniel
				Art Unit	Not Yet Assigned
j	(use as many sh	eets a	s necessary)	Examiner Name	Not Yet Assigned
Sheet	8	of	11	Attorney Docket Number	018865-015200US

			F	OREIGN	PATENT DOCL	JMENTS		
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		Country Code ³	· · · · · · · · · · · · · · · · · · ·	Kind Code [®] (il known)			Appear	T°
A.M	KN	PCT /	WO 01/95398	A1	12-13-2001	General Semiconductor, Inc.		
1	ко	PCT /	WO 02/01644	A2	01-03-2002	Silicon Wireless Corporation		
	KP	PCT /	WO 02/047171	A1	06-13-2002	International Rectifier Corporation	<u> </u>	

Examiner Signature	ANH	D.	MAi	Date Considered	10	17	2005

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		NON PATENT LITERATURE DOCUMENTS						
Examiner Initials *	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.						
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		NON PATENT LITERATURE DOCUMENTS						
Examiner Cite No.1		Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.						
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